Ref #	Hits	Search Query	DBs .	Default Operator	Plurals	Time Stamp
L1	2931	(polysilicon near10 channel) and amorphous	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/16 15:52
L2	1974	(tft or (thin near film)) and (polysilicon near10 channel) and amorphous	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/16 15:52
L3	1294	(tft or (thin near film)) same (polysilicon near10 channel) and amorphous	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/16 15:52
L4	552	(tft or (thin near film)) same (polysilicon near10 channel) same amorphous	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/16 15:52
<b>L</b> 5	99	(tft or (thin near film)) same (polysilicon near10 channel) same (amorphous near5 region)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/16 15:54
L6	59	(tft or (thin near film)) same (polysilicon near10 channel) same (amorphous near5 region) and (low near temperature)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/16 15:54
L7	18	(tft or (thin near film)) same (polysilicon near10 channel) same (amorphous near5 region) and (low near temperature) and (hot near carrier)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/16 15:57
L8	4	(tft or (thin near film)) same (polysilicon near10 channel) same (amorphous near5 region) and (low near temperature) and ((hot near carrier) near10 amorphous)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/16 15:55

7/16/07 5:08:58 PM
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L10	5	I9 and ((hot near carrier) near10 amorphous)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/16 15:56
<b>L11</b>	5	I9 and ((hot near carrier) with amorphous)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/16 15:56
L12	2820	Itps ((hot near carrier) with amorphous)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/16 15:56
L13	5	Itps and ((hot near carrier) with amorphous)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/16 15:56
L14	10	tft and ((hot near carrier) with amorphous)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/16 15:56
L15	2791	ltps	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/16 15:58
L16	110	Itps and (polysilicon near5 channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/16 15:58
L17	15	Itps and (polysilicon near5 channel) and (amorphous near2 region)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/16 15:58
L18	11	Itps and (polysilicon near5 channel) and (amorphous near region)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/16 15:58

7/16/07 5:08:58 PM C:\Documents and Settings\FErdem\My Documents\EAST\workspaces\10710844\_case.wsp

Page 3

L20	82	I19 and amorphous	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	<b>ON</b>	2007/07/16 16:00
L21	33	I19 and amorphous and carrier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/16 16:00
L22	6	I19 and (amorphous with carrier)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/16 16:03
L23		"6093586"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/16 16:05
L24	4	"6570552"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/16 16:07
L25	2553	(channel near2 polysilicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/16 16:07
L26	904	(channel near2 polysilicon) and amorphous	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/16 16:07
L27	38	(channel near2 polysilicon) and amorphous and (low near temperature near polysilicon near thin near film near transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/16 16:08
L28	37	(channel near2 polysilicon) and (amorphous near5 (film or layer or portion or region)) and (low near temperature near polysilicon near thin near film near transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/16 16:10

L29	12	(channel near2 polysilicon) and (amorphous near5 (film or layer or portion or region)) and (low near temperature near polysilicon near thin near film near transistor) and amorphous.clm. and polysilicon. clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/16 16:12
L30	71	(low near temperature near polysilicon near thin near film near transistor) and amorphous.clm. and polysilicon.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/16 16:13
L31	8	(low near temperature near polysilicon near thin near film near transistor) and amorphous.clm. and polysilicon.clm. and ohmic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/16 16:19
L32	<b>71</b>	(low near temperature near polysilicon near thin near film near transistor) and amorphous.clm. and polysilicon.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/16 16:22

7/16/07 5:08:58 PM C:\Documents and Settings\FErdem\My Documents\EAST\workspaces\10710844\_case.wsp

L34	17	I33 and (amorphous near (portion or region or section))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/16 16:30
L35	12	I33 and (amorphous near (portion or region or section)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/16 16:30
L36	2	133 and (amorphous near (portion or region or section)).clm. and (polysilicon near (portion or region or section)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/16 16:31
L37		I33 and (amorphous near2 (portion or region or section)).clm. and (polysilicon near2 (portion or region or section)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/16 16:32
L38	6	(tft or ltps-tft or ltpstft).clm. and (amorphous near2 (portion or region or section)).clm. and (polysilicon near2 (portion or region or section)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/16 16:34
L39	5	("20030061984" "20050019990")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/16 16:33
L40	6	(tft or ltps-tft or ltpstft).clm. and (amorphous near2 (portion or region or section)) same (polysilicon near2 (portion or region or section)) same channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/16 16:35
L41	167	(tft or ltps-tft or ltpstft).clm. and amorphous.clm. and polysilicon. clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/16 16:37
L42	4	(tft or ltps-tft or ltpstft).clm. and amorphous.clm. and polysilicon. clm. and (amorphous near10 carrier)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/16 16:37

7/16/07 5:08:58 PM C:\Documents and Settings\FErdem\My Documents\EAST\workspaces\10710844\_case.wsp Page 8

L44	12	I43 and (amorphous near portion)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/16 16:44
L45	8	l43 and (amorphous near portion). clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/16 16:45
L46	12	I43 and (amorphous near portion)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/16 16:46
L47	75	143 and (polysilicon or polycrystal or polycrystalline) and amorphous	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/16 16:46
L48	47	l43 and (channel near10 (polysilicon or polycrystal or polycrystalline)) and amorphous	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/16 16:54
L49	1843	(film or layer) with portion with (polysilicon or polycrystalline) with amorphous	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/16 16:54
L50	321	((film or layer) with portion with (polysilicon or polycrystalline) with amorphous).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/16 16:54
<b>L51</b>	19	((film or layer) with portion with (polysilicon or polycrystalline) with amorphous).clm. and tft.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/16 16:55

7/16/07 5:08:58 PM C:\Documents and Settings\FErdem\My Documents\EAST\workspaces\10710844\_case.wsp Page 10